



## BYT03-400

### HIGH EFFICIENCY ULTRAFAST DIODE

#### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	3 A
$V_{RRM}$	400 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	1.4 V
$t_{rr}(\text{max})$	25 ns

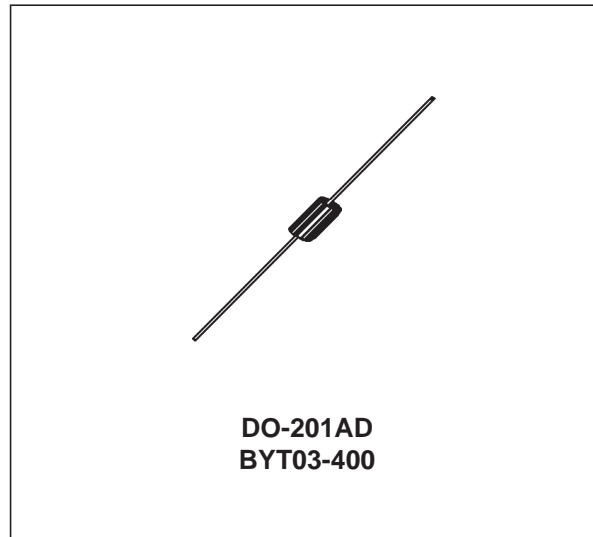
#### FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward & reverse recovery times

#### DESCRIPTION

The BYT03-400 which is using ST's 400V planar technology, is specially suited for switching mode base drive & transistor circuits.

The device, which is available in axial (DO-201AD) package, is also intended for use as a free wheeling diode in power supplies and other power switching applications.



#### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetive peak reverse voltage		400	V
$I_{F(AV)}$	Average forward current	$T_I = 55^\circ\text{C}$ $\delta = 0.5$	3	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ms}$ Sinusoidal	60	A
$T_{stg}$	Storage temperature range		- 65 to +150	°C
$T_j$	Maximum operating junction temperature		150	°C

## BYT03-400

### THERMAL PARAMETERS

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient*	20	°C/W

\* On infinite heatsink with 10mm lead length.

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameters	Test Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			20	$\mu\text{A}$
		$T_j = 100^\circ\text{C}$			0.2	0.5	mA
$V_F^{**}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 3\text{A}$			1.5	V
		$T_j = 100^\circ\text{C}$			1.0	1.4	

Pulse test: \*  $t_p = 5\text{ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380\mu\text{s}$ ,  $\delta < 2\%$

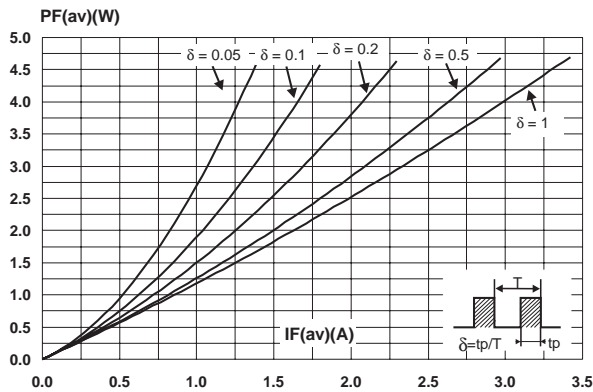
To evaluate the maximum conduction losses use the following equation:

$$P = 1.1 \times I_{F(AV)} + 0.08 I_{F(RMS)}^2$$

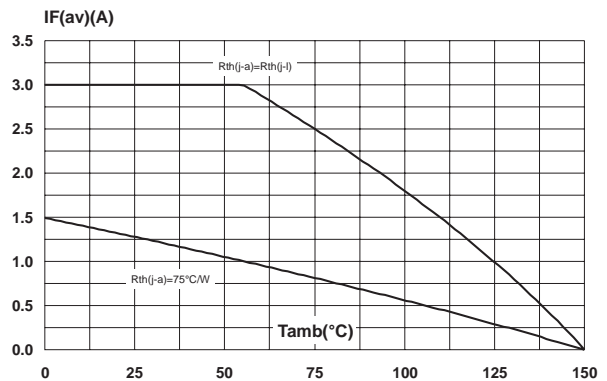
### DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$T_j = 25^\circ\text{C}$	$I_F = 0.5\text{A}$ $I_R = 1\text{A}$ $I_{rr} = 0.25\text{A}$		16	25	ns
			$I_F = 1\text{A}$ $di_F/dt = -15\text{A}/\mu\text{s}$ $V_R = 30\text{V}$			55	
$t_{fr}$	Forward recovery time	$T_j = 25^\circ\text{C}$	$I_F = 3\text{A}$ $di_F/dt = 50\text{A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$		75		ns
$V_{FP}$	Forward recovery voltage	$T_j = 25^\circ\text{C}$	$I_F = 3\text{A}$ $di_F/dt = 50\text{A}/\mu\text{s}$		7.0		V

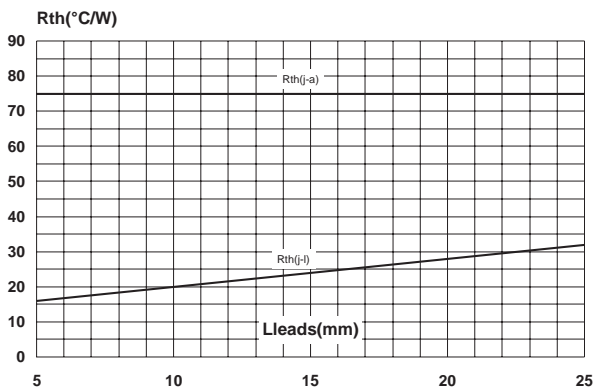
**Fig. 1:** Average forward power dissipation versus average forward current.



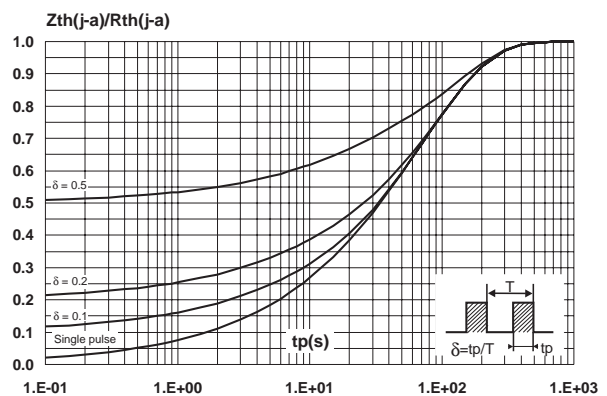
**Fig. 2:** Average forward current versus ambient temperature ( $\delta = 0.5$ )



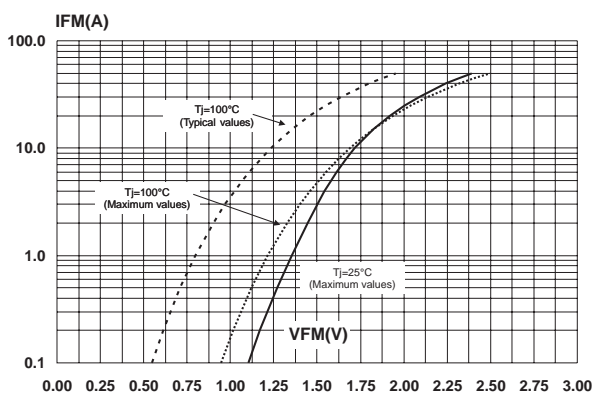
**Fig. 3:** Thermal resistance versus lead length.



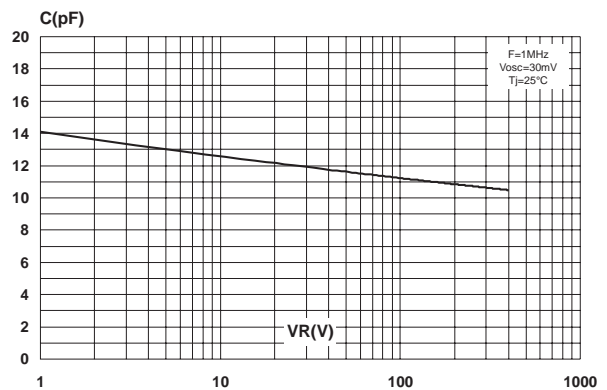
**Fig. 4:** Relative variation of thermal impedance junction ambient versus pulse duration (printed circuit board epoxy FR4, Leads = 10mm).



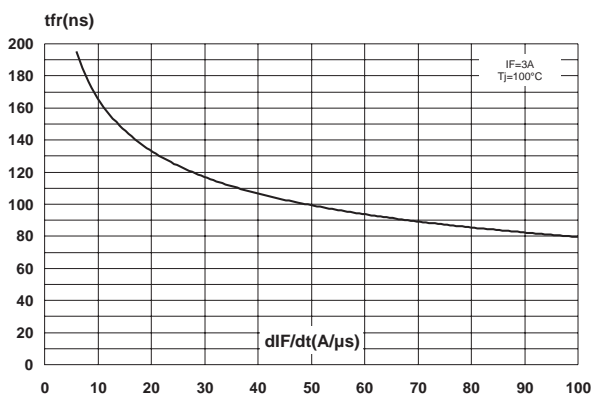
**Fig. 5:** Forward voltage drop versus forward current.



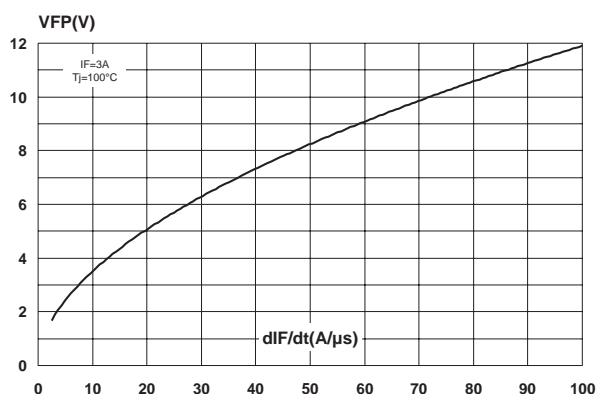
**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values).



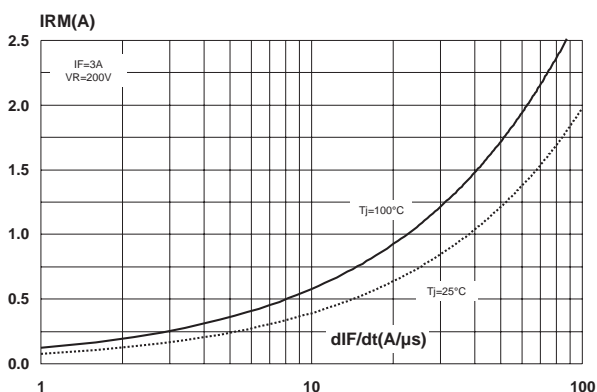
**Fig. 7:** Forward recovery time versus  $dI_F/dt$  (90% confidence).



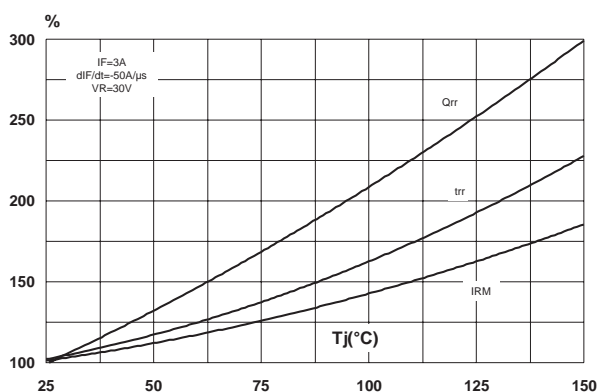
**Fig. 8:** Transient peak forward voltage versus  $dI_F/dt$  (90% confidence).



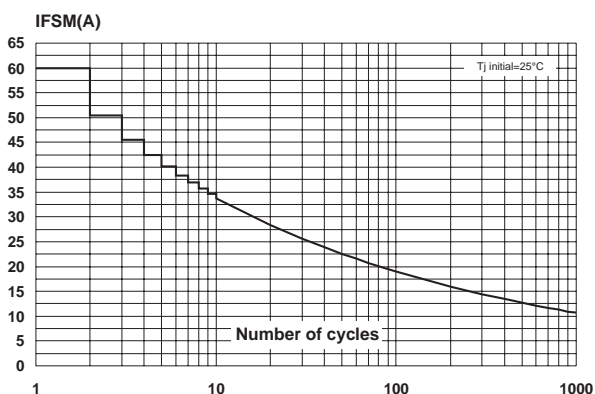
**Fig. 9:** Peak reverse recovery current versus  $dI_F/dt$  (90% confidence).



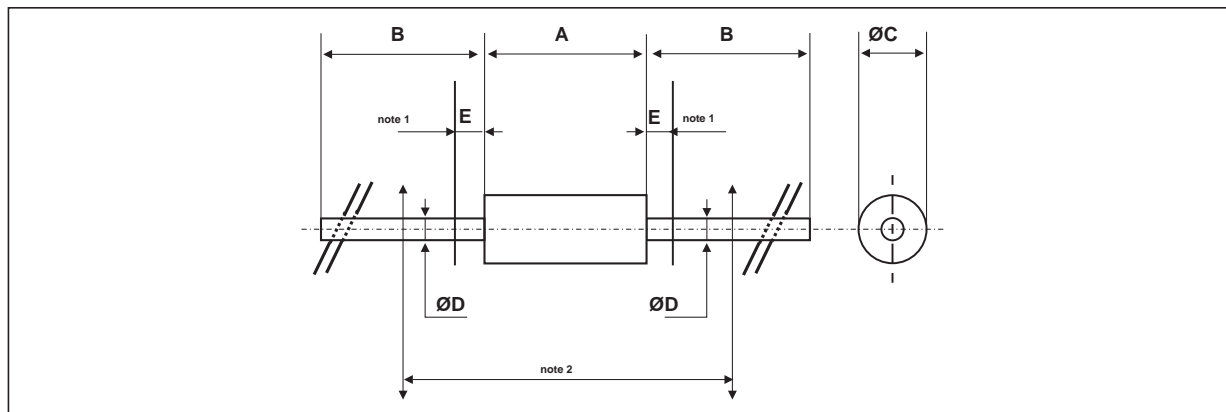
**Fig. 10:** Dynamic parameters versus junction temperature.



**Fig. 11:** Non repetitive surge peak current versus number of cycles.



**PACKAGE MECHANICAL DATA**  
DO-201AD



REF.	DIMENSIONS				NOTES
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A		9.50		0.374	1 - The lead diameter $\varnothing D$ is not controlled over zone E 2 - The minimum length which must stay straight between the right angles after bending is 0.59"(15 mm)
B	25.40		1.000		
C		5.30		0.209	
D		1.30		0.051	
E		1.25		0.049	

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYT03-400	BYT03-400	DO-201AD	1.16 g	600	Ammopack
BYT03-400RL	BYT03-400	DO-201AD	1.16 g	1900	Tape & Reel

- Cooling method: by conduction (method A)
- Epoxy meets UL 94,V0
- Bending method: Application note AN1471.

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